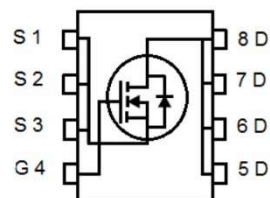


1. Description

SS080N10NS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

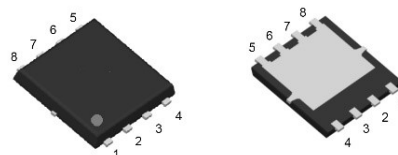
Schematic Diagram



KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	100	V
I_D	70	A
$R_{DS(on).typ}$	7.6	mΩ

PDFN5x6



FEATURES:

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 8m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS080N10NS	PDFN5x6	SS080N10NS	Reel